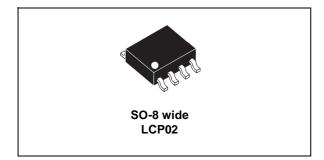


LCP02

Protection IC for ringing SLICs

Datasheet – production data



Features

- Protection IC recommended for ringing SLICs
- Wide firing voltage range: -120 V to +120 V
- Low gate triggering current: I_G = 5 mA max
- Peak pulse current: $I_{PP} = 30 \text{ A} (10/1000 \text{ } \mu\text{s})$
- Holding current: I_H = 150 mA min.

Applications

- Dual battery supply voltage SLICs
- Central office (CO)
- Private branch exchange (PBX)
- Digital loop carrier (DLC)
- Digital subscriber line access multiplexer (DSLAM)
- Fiber in the loop (FITL)
- Wireless local loop (WLL)
- Hybrid fiber coax (HFC)
- ISDN terminal adapter
- Cable modem

Description

The LCP02 has been developed to protect SLICs operating on both negative and positive battery supplies, as well as high voltage SLICs. It provides crowbar mode protection for both TIP and RING lines. The surge suppression is assumed for each wire by two thyristor structures, one dedicated to positive surges the second one for negative surges. Both positive and negative threshold levels are programmable by two gates.

LCP02 can be used to help equipment to meet various standards such as UL1950, IEC 60950 / CSAC22.2, UL1459 and TIA-968-A. LCP02 pinout and clearance is compatible with UL60950. Resin meets UL94 V0.

LCP02 is UL497B approved - file: E136224.

Figure 1. Functional diagram

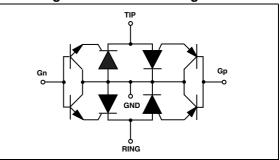
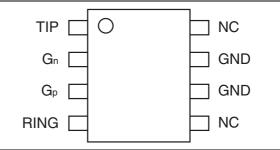


Figure 2. Pin-out configuration



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This is information on a product in full production.

1 Characteristics

Standard	Peak surge voltage (V)	Voltage waveform	Required peak current (A)	Current waveform	Minimum series resistor Rs to meet standard (Ω)		
GR-1089 Core First level	2500	2/10 µs	500	2/10 µs	20		
GR-1069 COTE FIIST LEVEL	1000	10/1000 µs	100	10/1000 µs	24		
GR-1089 Core Second level	5000	2/10 µs	500	2/10 µs	40		
GR-1089 Core Intra-building	1500	2/10 µs	100	2/10 µs	0		
	6000		150		94		
ITU-T-K20/K21	4000	10/700 µs	100	5/310 µs	49		
	1500		37.5		0		
ITU-T-K20 (IEC61000-4-2)	8000	1/60 ns	ESD conta	ct discharge	0		
110-1-K20 (IEC01000-4-2)	15000	1/00 115	ESD air discharge		0		
IEC61000-4-5	4000	10/700 µs	100	5/310 µs	49		
IEC01000-4-5	4000	1.2/50 µs	100	8/20 µs	0		
TIA 068 A (formarly ECC part 68) time A	1500	10/160 µs	200	10/160 µs	20		
TIA-968-A (formerly FCC part 68) type A	800	10/560 µs	100	10/560 µs	15		
TIA-968-A (formerly FCC part 68) type B	1000	9/720 µs	25	5/320 µs	0		

Table 1. Complia	nt with the follow	ving standards
		ning oluniaanao

Table 2. Absolute maximum ratings (T_{amb} = 25 °C)

Symbol	Parameter		Value	Unit
I _{PP}	Peak pulse current	10/1000 µs 5/310 µs 2/10µs	30 45 100	A
I _{TSM}	Non repetitive surge peak on-state current (F = 50 Hz) I_{TSM} value specified for each line I_{TSM} value can be applied on both lines at the same time (GND capability is twice the line I_{TSM})	$t_p = 0.2 \text{ s}$ $t_p = 1 \text{ s}$ $t_p = 15 \text{ min.}$	9 6 1.9	A
V _{Gn} V _{Gp}	Negative battery voltage range Positive battery voltage range			V
Тj	Operating junction temperature range			°C
T _{stg}	Storage temperature range			°C
TL	Lead solder temperature (10 s duration)		260	°C



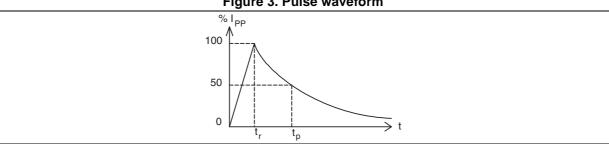


Figure 3. Pulse waveform

Table 3. Thermal resistance

Symbol	Parameter	Value	Unit
R _{th(j-a)}	Junction to ambient	150	°C/W

Table 4. Parameters related to the negative suppressor

Symbol	Parameter	Test conditions	Min.	Max.	Unit
I _{Gn}	Negative gate trigger current	V _{Gn/GND} = -60 V Measured at 50 Hz		5	mA
I _{H-}	Holding current (see Figure 4)	V _{Gn} = -60 V	150		mA
V _{DGL-}	Dynamic switching voltage Gn / TIP or RING ⁽¹⁾	$\begin{split} V_{Gn/GND} &= -60 \text{ V} \\ 10/700 \ \mu\text{s} & 2 \ \text{kV} \text{R}_{\text{s}} &= 25 \ \Omega \text{I}_{\text{PP}} &= 30 \ \text{A} \\ 1.2/50 \ \mu\text{s} & 2 \ \text{kV} \text{R}_{\text{s}} &= 25 \ \Omega \text{I}_{\text{PP}} &= 30 \ \text{A} \end{split}$		8 15	V

1. The V_{DGL} value is the difference between the peak line voltage during the surge and the programmed gate voltage.

Table 5. Parameters related to the positive suppressor

Symbol	Parameter	Test conditions		Max.	Unit
I _{Gp}	Positive gate trigger current	$V_{Gp/GND}$ = 60 V, measured at 50 Hz		5	mA
		V _{Gp/GND} = 60 V			
V_{DGL+}	Dynamic switching voltage Gp / TIP or RING ⁽¹⁾	10/700 μ s 2 kV R _s = 25 Ω I _{PP} = 30 A		8	V
		1.2/50 μ s 2 kV R _s = 25 Ω I _{PP} = 30 A		35	

1. The V_{DGL} value is the difference between the peak line voltage during the surge and the programmed gate voltage.

Table 6. Parameters related to TIP or RING / GND

Symbol	Parameter	Test conditions	Min.	Max.	Unit
۱ _R	Reverse leakage current	$V_{\text{TIP or RING}} = +120 \text{ V} V_{\text{Gp/TIP or RING}} = +1 \text{ V}$ $V_{\text{TIP or RING}} = -120 \text{ V} V_{\text{Gn/TIP or RING}} = -1 \text{ V}$		5 5	μA
С	Capacitance TIP or RING / GND	V_R = -3 V, F =1 MHz, V_{Gp} = 60 V, V_{Gn} = -60 V		60	pF



Table 11 Recommended gate capacitance						
Symbol	Component	Min.	Тур.	Max.	Unit	
C _n , C _p	Gate decoupling capacitance	100	220		nF	

Table 7. Recommended gate capacitance

Figure 4. Relative variation of holding current versus junction temperature

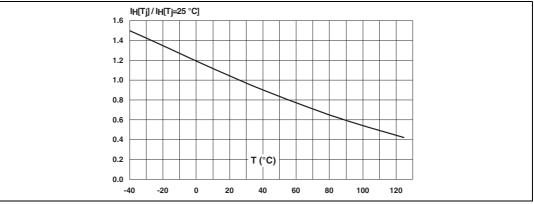


Figure 5. Maximum non repetitive surge peak on state current versus overload duration

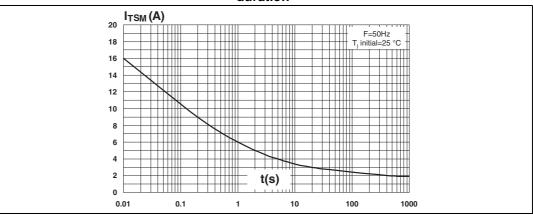
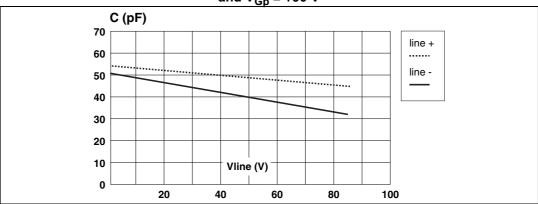


Figure 6. Capacitance versus reverse applied voltage (typical values) with V_{Gn} = -90 V and V_{Gp} = +90 V



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2 Technical information

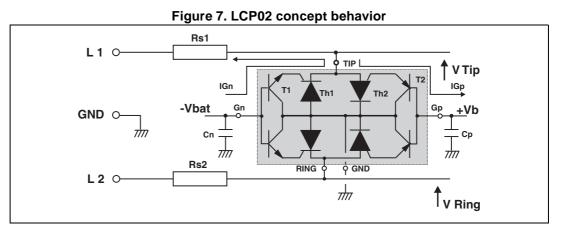


Figure 7 shows the classical protection circuit using the LCP02 crowbar concept. This topology has been developed to protect two-battery voltage SLICs. It allows both positive and negative firing thresholds to be programmed. The LCP02 has two gates (Gn and Gp). Gn is biased to negative battery voltage -Vbat, while Gp is biased to the positive battery voltage +Vb.

When a negative surge occurs on one wire (L1 for example), a current IGn flows through the base of the transistor T1 and then injects a current in the gate of the thyristor Th1 which turns-on. All the surge current flows through the ground. After the surge, when the current flowing through Th1 becomes less negative than the negative holding current I_{H-} , Th1 switches off. This holding current I_{H-} is temperature dependent as per *Figure 4*

When a positive surge occurs on one wire (L1 for example), a current IGp flows through the base of the transistor T2 and then injects a current in the gate of the thyristor Th2 which fires. All the surge current flows through the ground. After the surge, when the current flowing through Th2 becomes less positive than the positive holding current I_{H+} , Th2 switches off. This holding current I_{H+} , typically 20 mA at 25 °C, is temperature dependent and the same *Figure 4* also applies.

The capacitors Cn and Cp are used to speed up the crowbar structure firing during the fast rise or fall edges. This allows minimization of the dynamic breakover voltage at the SLIC TIP and RING inputs during fast surges. Please note that these capacitors are generally available around the SLIC. To be efficient they have to be as close as possible to the LCP02 gate pins (Gn and Gp) and to the reference ground track (or plan). The optimized value for Cn and Cp is 220 nF.

The series resistors Rs shown in *Figure* 7 represent the fuse resistors or the PTCs which are needed to withstand the power contact or the power induction tests imposed by the country standards. Taking this factor into account, the actual lightning surge current flowing through the LCP02 is equal to:

I surge = Vsurge / (Rg + Rs)

With

V surge = peak surge voltage imposed by the standard.

Rg = series resistor of the surge generator

Rs = series resistor of the line card (e.g. PTC)



For a line card with 50 Ω of series resistors which has to be qualified under GR-1089 1000 V 10/1000 µs surge, the present current through the LCP02 is equal to:

The LCP02 topology is particularly optimized for the new telecom applications such as fiber in the loop, WLL systems, and decentralized central office, for example.

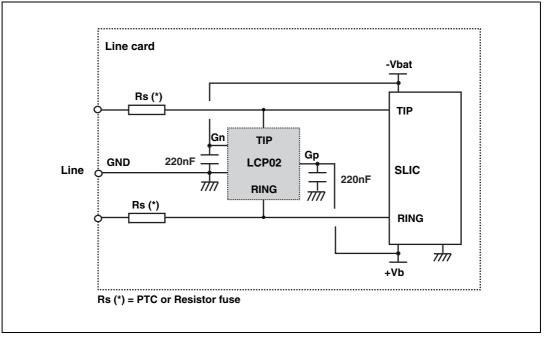


Figure 8. Protection of SLIC with positive and negative battery voltages

Figure 8 shows the classical protection topology for SLIC using both positive and negative battery voltages. With such a topology the SLIC is protected against surge over +Vb and lower than -Vbat. In this case, +Vb can be programmed up to +120 V while -Vbat can be programmed down to -120 V.

3 Package information

- Epoxy meets UL94, V0
- Lead-free package

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: <u>www.st.com</u>. ECOPACK[®] is an ST trademark.

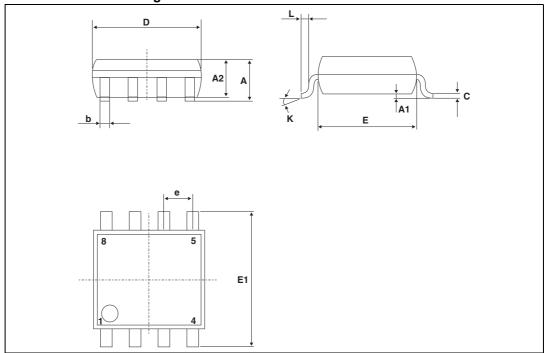


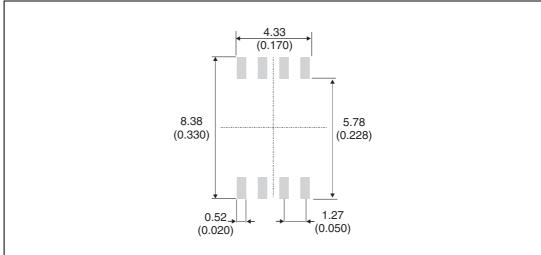
Figure 9. SO-8 wide dimension definitions



			Dimer	nsions			
Ref.		Millimeters			Inches		
	Min.		Max.	Min.		Max.	
А	1.70	1.90	2.10	0.07	0.07	0.08	
A1	0.05	0.10	0.25	0.00	0.00	0.01	
A2	1.65	1.80	1.75	0.06	0.07	0.07	
b	0.38	0.43	0.48	0.01	0.02	0.02	
С	0.15	0.20	0.25	0.01	0.01	0.01	
D	5.14	5.24	5.34	0.02	0.021	0.21	
Е	5.20	5.30	5.40	0.02	0.021	0.21	
E1	7.70	7.80	8.25	0.30	0.031	0.32	
е		1.27		0.05	0.05		
K			8.00	0.14	0.31		
L	0.55	0.75	0.85	0.02	0.03	0.03	

Table 8. SO-8 wide dimension values

Figure 10. SO-8 wide footprint in mm (inches)





4 Ordering information

Table 9.	Ordering	information
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Oi	der code	Marking	Package	Weight	Base qty	Delivery mode
LCP	02-150B1RL	LCP02	SO-8 wide	0.125g	1500	Tape and reel

5 Revision history

Date	Revision	Changes
20-Mar-2014	1	First release



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